



2SK2417

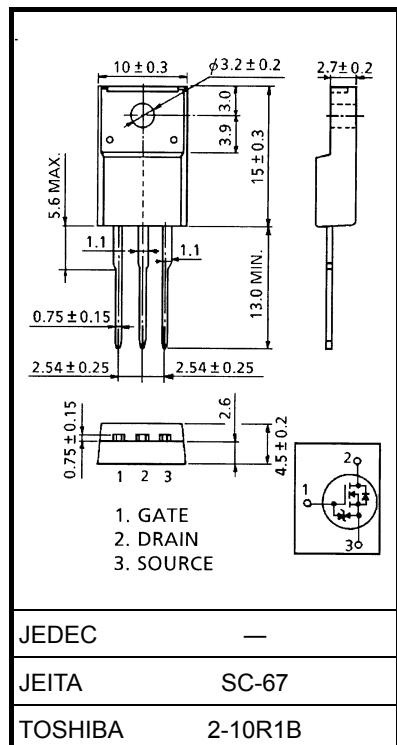
Chopper Regulator, DC-DC Converter and Motor Drive Applications

Unit: mm

- Low drain-source ON resistance : $R_{DS\text{ (ON)}} = 0.42 \Omega$ (typ.)
- High forward transfer admittance : $|Y_{fs}| = 7.5 \text{ S}$ (typ.)
- Low leakage current : $I_{DSS} = 100 \mu\text{A}$ (max) ($V_{DS} = 250 \text{ V}$)
- Enhancement mode : $V_{th} = 1.5$ to 3.5 V ($V_{DS} = 10 \text{ V}$, $I_D = 1 \text{ mA}$)

Absolute Maximum Ratings ($T_a = 25^\circ\text{C}$)

Characteristics	Symbol	Rating	Unit
Drain-source voltage	V_{DSS}	250	V
Drain-gate voltage ($R_{GS} = 20 \text{ k}\Omega$)	V_{DGR}	250	V
Gate-source voltage	V_{GSS}	± 20	V
Drain current	DC (Note 1)	I_D	A
	Pulse (Note 1)	I_{DP}	A
Drain power dissipation ($T_c = 25^\circ\text{C}$)	P_D	30	W
Single pulse avalanche energy (Note 2)	E_{AS}	110	mJ
Avalanche current	I_{AR}	7.5	A
Repetitive avalanche energy (Note 3)	E_{AR}	3	mJ
Channel temperature	T_{ch}	150	$^\circ\text{C}$
Storage temperature range	T_{stg}	-55~150	$^\circ\text{C}$



Weight: 1.9 g (typ.)

Note: Using continuously under heavy loads (e.g. the application of high temperature/current/voltage and the significant change in temperature, etc.) may cause this product to decrease in the reliability significantly even if the operating conditions (i.e. operating temperature/current/voltage, etc.) are within the absolute maximum ratings. Please design the appropriate reliability upon reviewing the Toshiba Semiconductor Reliability Handbook ("Handling Precautions"/Derating Concept and Methods) and individual reliability data (i.e. reliability test report and estimated failure rate, etc).

Thermal Characteristics

Characteristics	Symbol	Max	Unit
Thermal resistance, channel to case	$R_{th\text{ (ch-c)}}$	4.16	$^\circ\text{C} / \text{W}$
Thermal resistance, channel to ambient	$R_{th\text{ (ch-a)}}$	62.5	$^\circ\text{C} / \text{W}$

Note 1: Ensure that the channel temperature does not exceed 150°C .

Note 2: $V_{DD} = 50 \text{ V}$, $T_{ch} = 25^\circ\text{C}$ (initial), $L = 3.3 \text{ mH}$, $R_G = 25 \Omega$, $I_{AR} = 7.5 \text{ A}$

Note 3: Repetitive rating: pulse width limited by maximum channel temperature

This transistor is an electrostatic-sensitive device.
Please handle with caution.

Electrical Characteristics ($T_a = 25^\circ C$)

Characteristics	Symbol	Test Condition	Min	Typ.	Max	Unit	
Gate leakage current	I_{GSS}	$V_{GS} = \pm 16 V, V_{DS} = 0 V$	—	—	± 10	μA	
Drain cut-off current	I_{DSS}	$V_{DS} = 250 V, V_{GS} = 0 V$	—	—	100	μA	
Drain-source breakdown voltage	$V_{(BR) DSS}$	$I_D = 10 mA, V_{GS} = 0 V$	250	—	—	V	
Gate threshold voltage	V_{th}	$V_{DS} = 10 V, I_D = 1 mA$	1.5	—	3.5	V	
Drain-source ON resistance	$R_{DS (ON)}$	$V_{GS} = 10 V, I_D = 3.5 A$	—	0.42	0.5	Ω	
Forward transfer admittance	$ Y_{fs} $	$V_{DS} = 10 V, I_D = 3.5 A$	4	7.5	—	S	
Input capacitance	C_{iss}	$V_{DS} = 10 V, V_{GS} = 0 V, f = 1 MHz$	—	700	—	pF	
Reverse transfer capacitance	C_{rss}		—	80	—		
Output capacitance	C_{oss}		—	270	—		
Switching time	Rise time	t_r	 V_{GS} 10V 0V 1.5Ω $I_D = 3.5A$ V_{OUT} $R_L = 28.6\Omega$ $V_{DD} \approx 100V$ Duty $\leq 1\%$, $t_W = 10\mu s$	—	10	—	ns
	Turn-on time	t_{on}		—	20	—	
	Fall time	t_f		—	10	—	
	Turn-off time	t_{off}		—	70	—	
Total gate charge (Gate-source plus gate-drain)	Q_g	$V_{DD} \approx 200 V, V_{GS} = 10 V, I_D = 7.5 A$	—	20	—	nC	
Gate-source charge	Q_{gs}		—	13	—		
Gate-drain ("miller") charge	Q_{gd}		—	7	—		

Source-Drain Ratings and Characteristics ($T_a = 25^\circ C$)

Characteristics	Symbol	Test Condition	Min	Typ.	Max	Unit
Continuous drain reverse current (Note 1)	I_{DR}	—	—	—	7.5	A
Pulse drain reverse current (Note 1)	I_{DRP}	—	—	—	30	A
Forward voltage (diode)	V_{DSF}	$I_{DR} = 7.5 A, V_{GS} = 0 V$	—	—	-2.0	V
Reverse recovery time	t_{rr}	$I_{DR} = 7.5 A, V_{GS} = 0 V$ $dI_{DR} / dt = 100 A / \mu s$	—	180	—	ns
Reverse recovery charge	Q_{rr}		—	1.1	—	μC

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